

Supplemental Information for

Effect of Al₂O₃ Buffer Layers on the Properties of Sputtered VO₂ Thin Films

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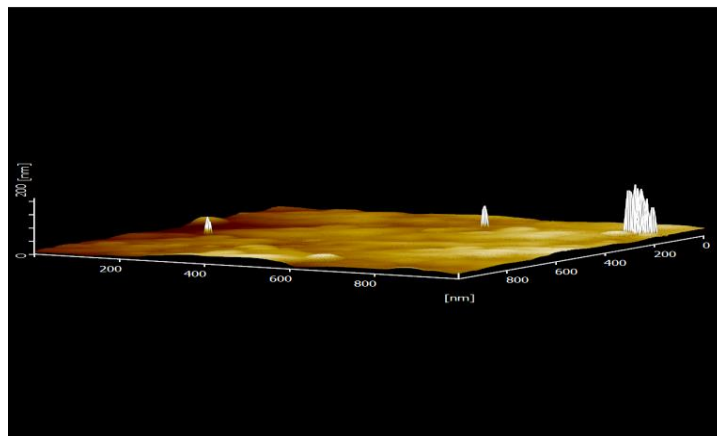


Figure S1 The AFM image of Al₂O₃ thin film

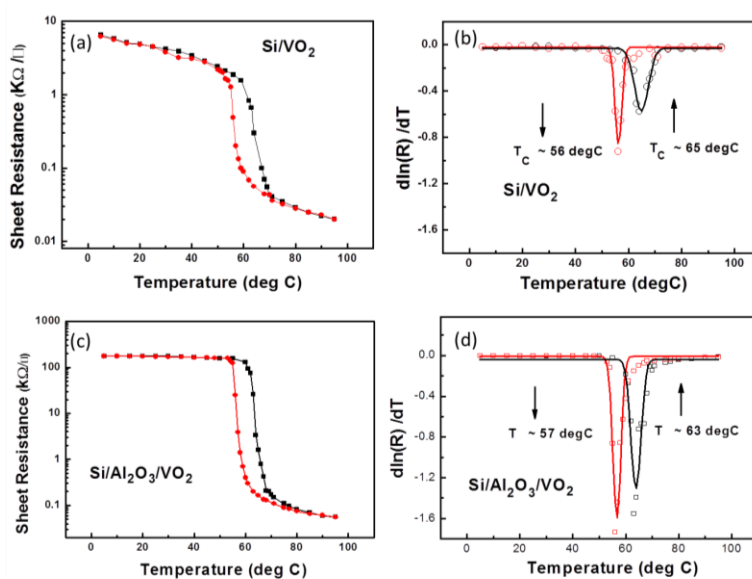


Figure S2 Sheet resistance of **a** Si/VO₂ and **c** Si/Al₂O₃/VO₂ grown under 5% oxygen partial pressure as a function of temperature, **b** and **d** shows the derivatives of the curves in **a** and **c** respectively.

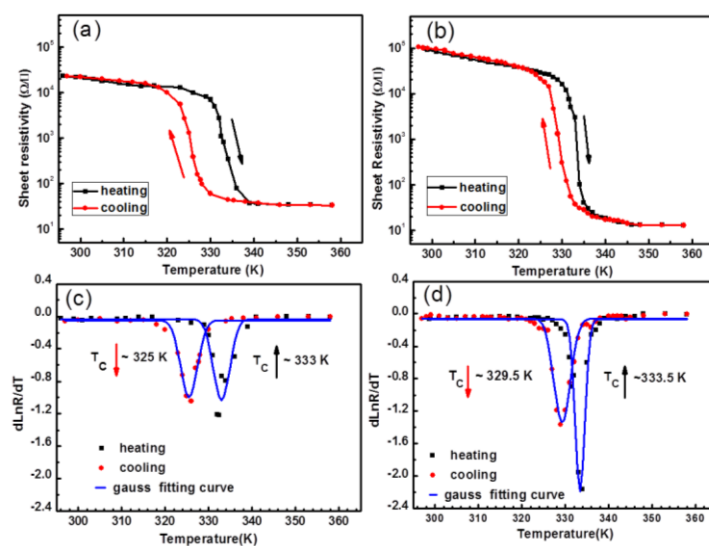


Figure S3 Sheet resistance of **a** Si/VO₂ and **b** Si/Al₂O₃/VO₂ grown under 4% oxygen partial pressure as a function of temperature, **c** and **d** shows the derivatives of the curves in **a** and **c** respectively.